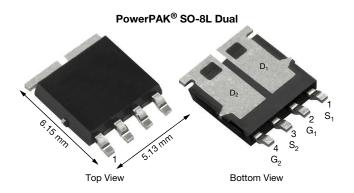


Vishay Siliconix

Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	60		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.012		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.016		
I _D (A) per leg	30		
Configuration	Dual		
Package	PowerPAK SO-8L		

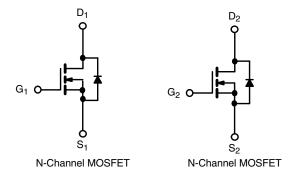
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	60		
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C ^a	- I _D	30		
	T _C = 125 °C		26		
Continuous Source Current (Diode conduction) ^a		I _S	30	Α	
Pulsed Drain Current b		I _{DM}	84		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	23	1	
Single Pulse Avalanche Energy	L = U.1 Min	E _{AS}	26.5	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	48	W	
	T _C = 125 °C		16		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak temperature) d, e		-	260	C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB mount ^c	R_{thJA}	85	°C/W	
unction-to-Case (Drain)		R_{thJC}	3.1	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static							'
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2.0	2.5	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 10 A	-	0.0100	0.0120	Ω
	В	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.0191	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.0235	
		V _{GS} = 4.5 V	I _D = 8 A	-	0.0131	0.0160	
Forward Transconductance b	g _{fs}	V_{DS}	= 15 V, I _D = 10 A	-	43	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	=.	1228	1600	pF
Output Capacitance	Coss	$V_{GS} = 0 V$		=.	506	660	
Reverse Transfer Capacitance	C _{rss}			=.	28	40	
Total Gate Charge ^c	Qg		V _{DS} = 30 V, I _D = 1.5 A	=.	18	30	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$		-	3.5	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	2.5	-	
Gate Resistance	R _g	f = 1 MHz		0.25	0.52	0.80	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	10	20	
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_{L} = 20 \Omega$ $I_{D} \cong 1.5 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	3	10	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	23	40	
Fall Time ^c	t _f			-	25	40	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			=.	-	84	Α
Forward Voltage	V_{SD}	I _F = 10 A, V _{GS} = 0 V		_	0.84	1.2	V

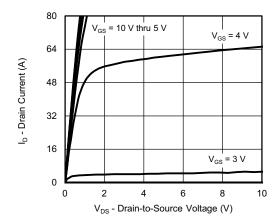
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

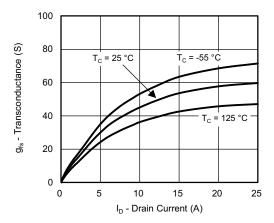
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



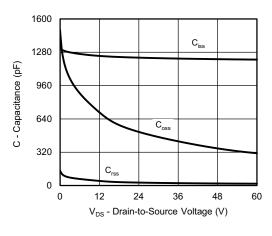
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



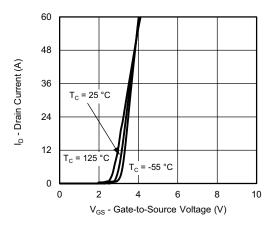
Output Characteristics



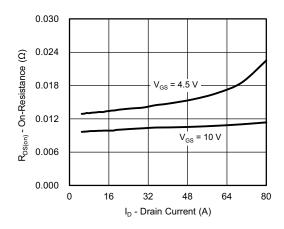
Transconductance



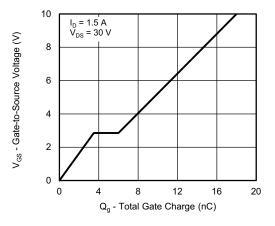
Capacitance



Transfer Characteristics



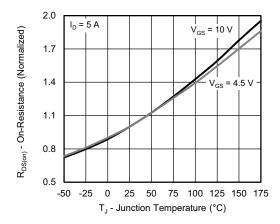
On-Resistance vs. Drain Current



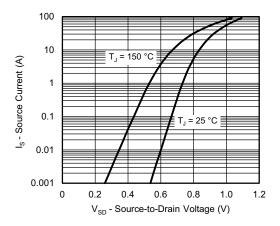
Gate Charge



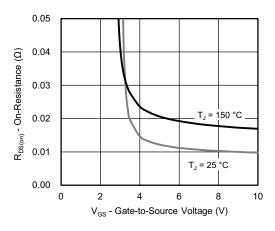
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



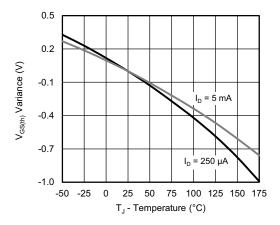
On-Resistance vs. Junction Temperature



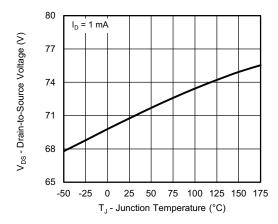
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



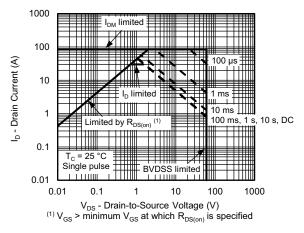
Threshold Voltage



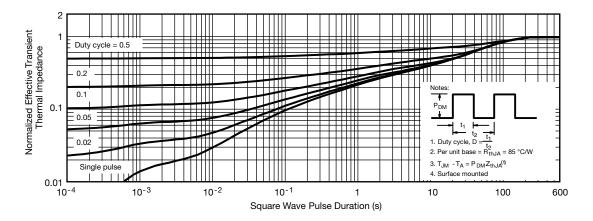
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Safe Operating Area

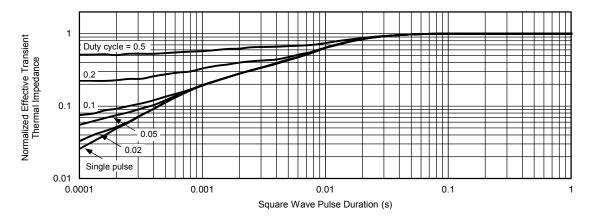


Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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